SURFACE MOUNT GLASS PASSIVATED FAST RECOVERY SILICON RECTIFIERS

Reverse Voltage - 50 to 600 V Forward Current - 1 A

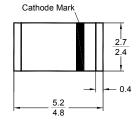
Features

- · Fast switching
- · Glass passivated device
- Ideal for surface mounted applications
- · Low leakage current
- Metallurgically bonded construction

Mechanical Data

· Case: MELF (DO-213AB) molded plastic

· Mounting position: Any



Plastic case MELF (DO-213AB) Dimensions in mm

Absolute Maximum Ratings and Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz. resistive or inductive load. For capacitive load, derate current by 20%.

Parameter		Symbols	SM4933	SM4934	SM4935	SM4936	SM4937	Units
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	50	100	200	400	600	V
Maximum RMS Voltage		V_{RMS}	35	70	140	280	420	V
Maximum DC Blocking Voltage		V_{DC}	50	100	200	400	600	V
Maximum Average Forward Rectified Current (at T _A = 55 °C)		I _{F(AV)}	1					Α
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)		I _{FSM}	30				Α	
Maximum Forward Voltage at 1 A		V _F	1.2			V		
Maximum Average Reverse Current at Rated DC Blocking Voltage	at T _A = 25 °C	I _R	5				μА	
	at T _A = 125 °C		100					
Maximum Reverse Recovery Time 4)		t _{rr}	200					ns
Typical Junction Capacitance 1)		Сл	15				pF	
Maximum Thermal Resistance		$R_{ heta JA} \ R_{ heta JL}$	30 ²⁾ 75 ³⁾				°C/W	
Operating and Storage Temperature Range		T_j , T_{stg}	- 65 to + 175					°C

¹⁾ Measured at 1 MHz and applied reverse voltage of 4 V DC.

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²⁾ Thermal resistance junction to terminal 6 mm² copper pads to each terminal.

³⁾ Thermal resistance from junction to ambient 6 mm² copper pads to each terminal.

 $^{^{4)}}$ Test conditions: I_F = 1 A, V_R = 30 V.

